

CDST226-G RoHS Device



Features

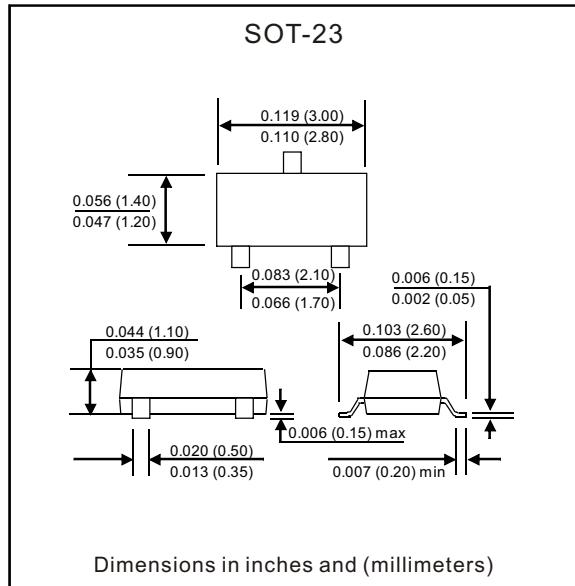
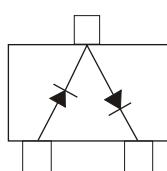
-Power dissipation: 150mW (@TA=25°C)

Mechanical data

Case: SOT-23

Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.

Marking: C3



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Symbol	Limits	Unit
Non-Repetitive peak reverse voltage	V _{RM}	85	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V _{RRM} V _{RWM} V _R	80	V
Forward continuous current	I _{FM}	300	mA
Average rectified output current	I _O	100	mA
Peak forward surge current @1μS @1.0S	I _{FSM}	2	A
Power dissipation	P _D	150	mW
Storage temperature range	T _{STG}	-55 ~ +125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Reverse breakdown voltage	V _{BR}	I _R =100μA	80		V
Reverse leakage current	I _R	V _R =80V		0.5	μA
Forward voltage	V _F	I _F =100mA		1.2	V
Diode capacitance	C _T	V _R =0V, f=1MHz		3	pF
Reverse recovery time	t _{rr}			4	nS

SMD Switching Diode

COMCHIP
SMD Diodes Specialist

Electrical and Characteristic Curves (CDST226-G)

Fig. 1 - Forward Characteristics

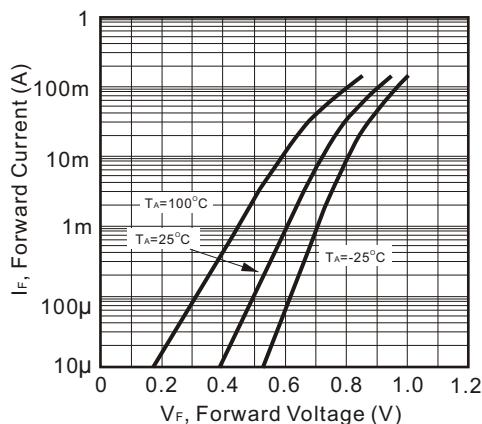


Fig. 2 - Reverse Characteristics

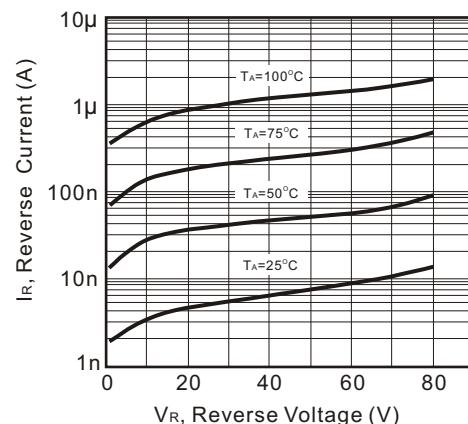


Fig. 3 - Diode Capacitance

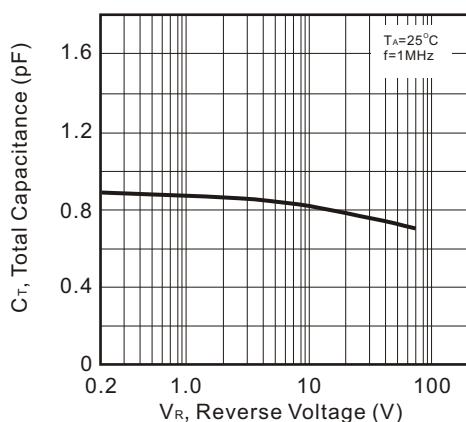


Fig. 4 - Reverse Recovery Characteristics

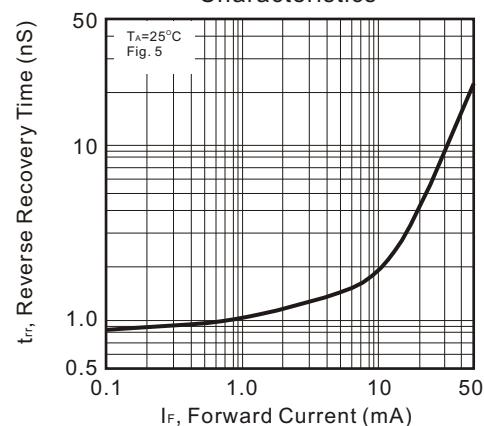


Fig. 5 - Reverse Recovery Time (t_{rr}) Test Circuit

